

General Description

The WSK290N04G6 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK290N04G6 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

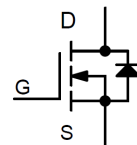
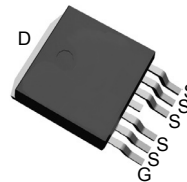
Product Summary

BVDSS	RDSON	ID
40V	1.2mΩ	290A

Applications

- Switching application
- Power Management for Inverter Systems.

TO-263-6L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)			
V _{DSS}	Drain-Source Voltage	40	V
V _{GSS}	Gate-Source Voltage	±20	
T _J	Maximum Junction Temperature	175	°C
T _{STG}	Storage Temperature Range	-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C 190	A
Mounted on Large Heat Sink			
I _{DM}	Pulsed Drain Current ¹	T _C =25°C 1015	A
I _D	Continuous Drain Current	T _C =25°C 290	A
		T _C =100°C 207	
P _D	Maximum Power Dissipation	T _C =25°C 230	W
		T _C =100°C 115	
R _{θJC}	Thermal Resistance-Junction to Case	0.65	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient	50	
Avalanche Ratings			
E _{AS}	Avalanche Energy, Single Pulsed	L=0.5mH 1400	mJ

NOTE:

1, Pulse width limited by maximum junction temperature.

2, UIS tested and pulse width limited by maximum junction temperature (initial temperature T_J=25°C).

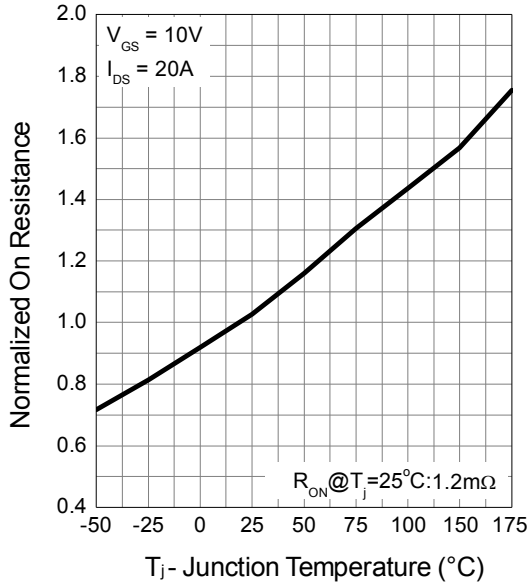
Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V T _J =85°C	-	-	1	μA
			-	-	10	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.0	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =30A	-	1.2	1.6	mΩ
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =20A	-	1.5	2.5	mΩ
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =104A, dI _{SD} / dt=100A/μs	-	45	-	ns
Q _{rr}	Reverse Recovery Charge		-	98	-	nC
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.0	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, Frequency=1.0MHz	-	8102	-	pF
C _{oss}	Output Capacitance		-	945	-	
C _{riss}	Reverse Transfer Capacitance		-	410	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, R _G =6 Ω, I _{DS} =20A, V _{GS} =10V .,	-	29	-	ns
T _r	Turn-on Rise Time		-	17	-	
t _{d(OFF)}	Turn-off Delay Time		-	150	-	
T _f	Turn-off Fall Time		-	65	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _{DS} =20A	-	142	-	nC
Q _{gs}	Gate-Source Charge		-	34	-	
Q _{gd}	Gate-Drain Charge		-	25	-	

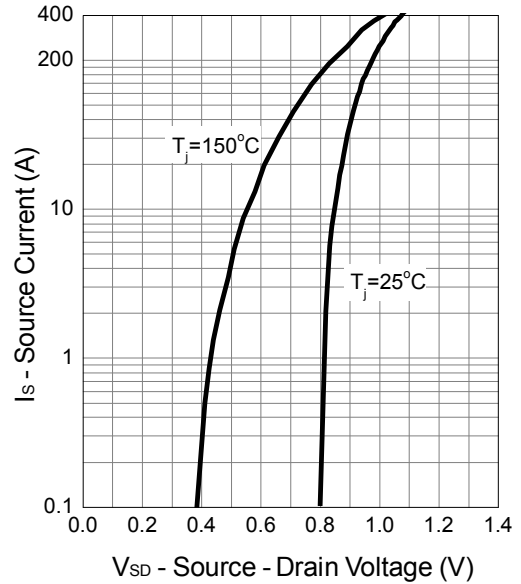
Note * : Pulse test ; pulse width ≤300μs, duty cycle ≤2%.

Typical Characteristics

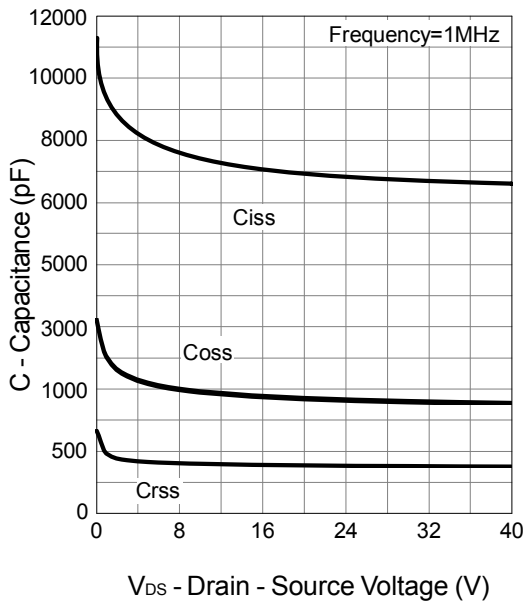
Drain-Source On Resistance



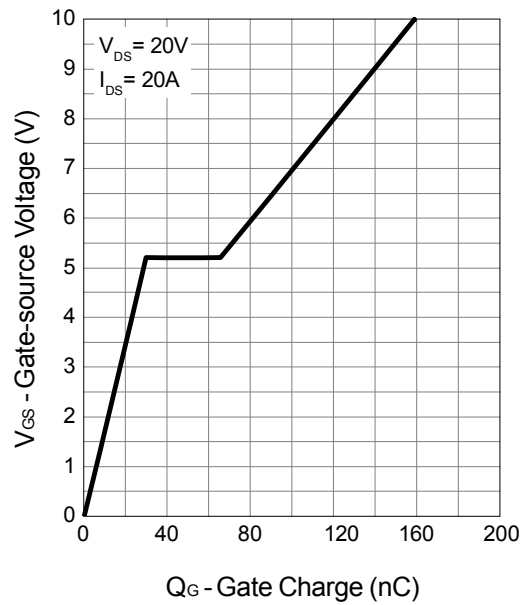
Source-Drain Diode Forward



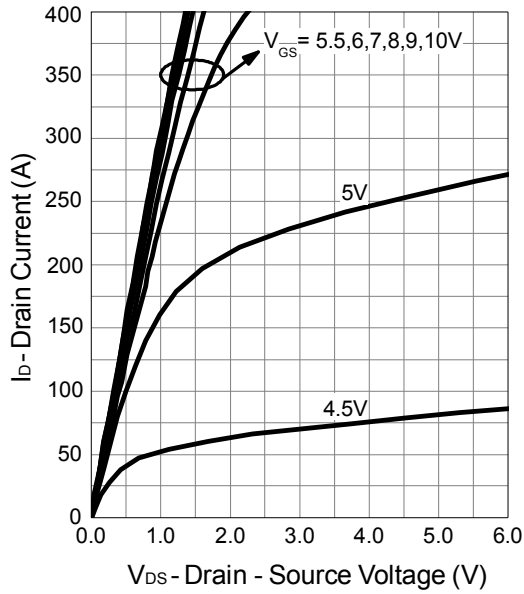
Capacitance



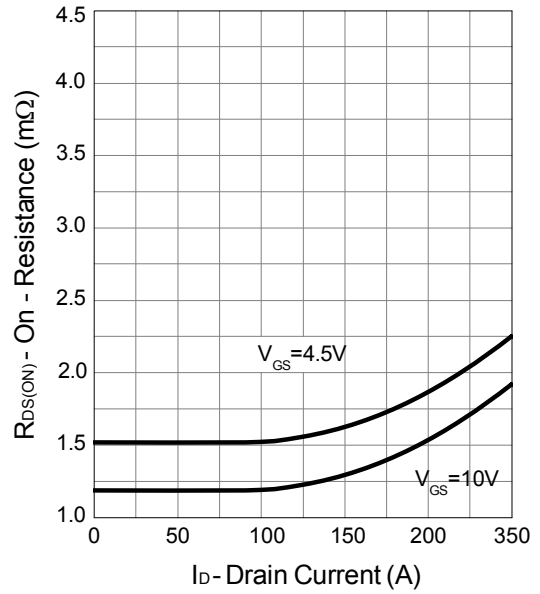
Gate Charge



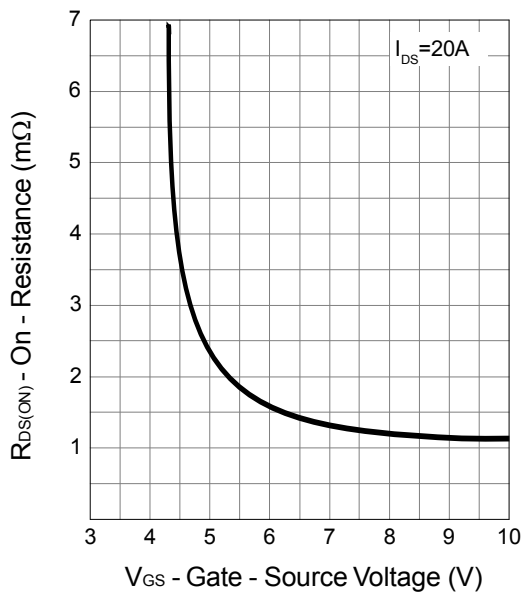
Output Characteristics



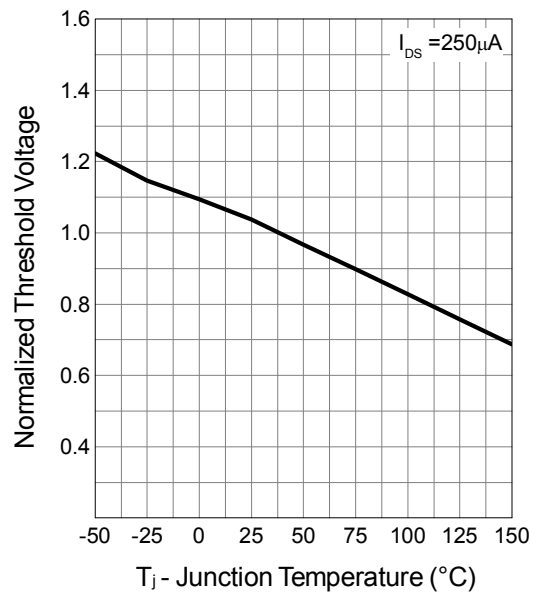
Drain-Source On Resistance

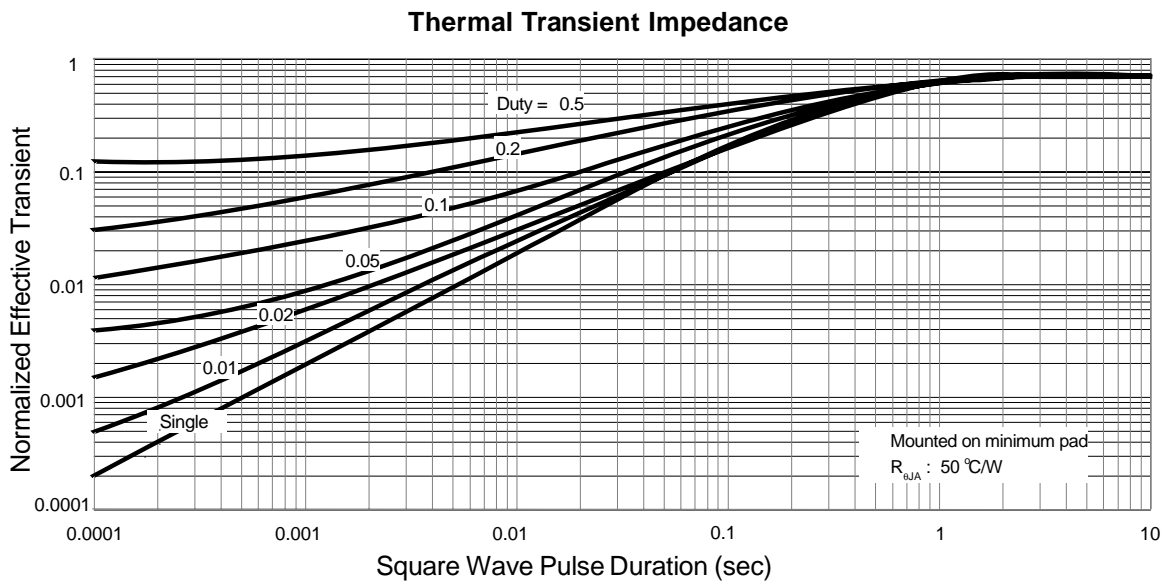
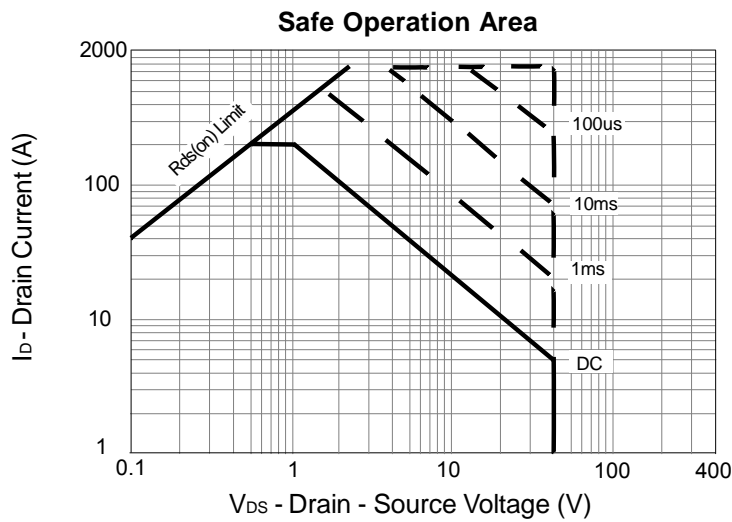
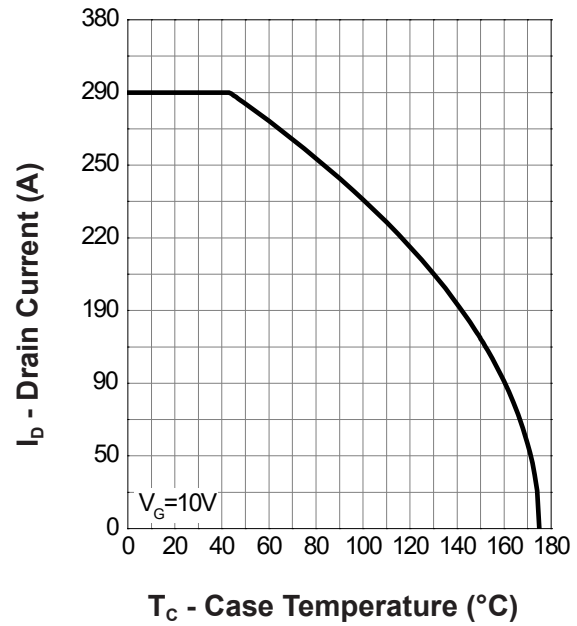
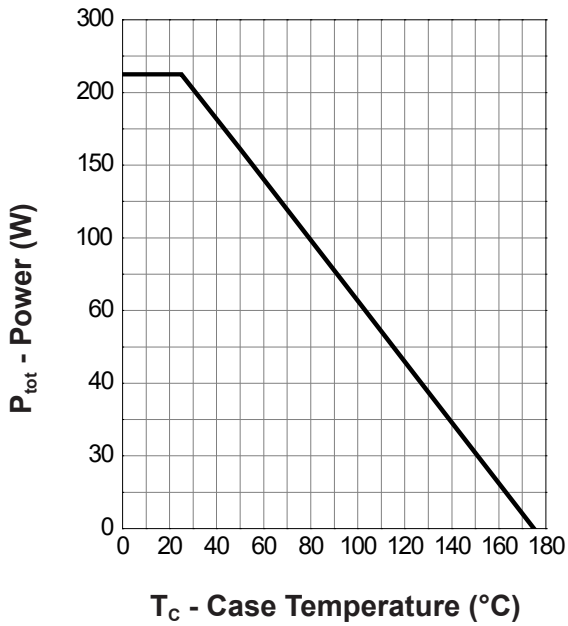


Gate-Source On Resistance



Gate Threshold Voltage







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